Kondo excitons in self-assembled quantum dots

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Abstract

We describe novel excitons in quantum dots by allowing for an interaction with a Fermi sea of electrons. We argue that these excitons can be realized very simply with self-assem bled quantum dots, using the wetting layer as host for the Fermi sea. We show that a tunnel hybridization of a charged exciton with the Fermi sea leads to two striking elects in the optical spectra. First, the photolum inescence lines become strongly dependent on the vertical bias. Secondly, if the exciton spin is nonzero, the K ondo elect leads to peculiar photolum inescence line shapes with a line width determ ined by the K ondo temperature.

The K ondo e ect concerns the interaction of a localized spin with a Ferm i æa of electrons [1]. It is a crucial e ect in various areas of nanophysics where often a nano-sized object with spin is in close proximity to a metal [2]. Sem iconductor nanostructures are ideal for investigations of K ondo physics because, in contrast to metals, their properties are voltagetunable [3]. Characteristic to the K ondo e ect are a screening of the localized spin and a resonance in the quasi-particle density of states (DOS) at the Ferm i energy. This leads to a maximum in conductance at very low temperatures in the transport through a spin- $\frac{1}{2}$ quantum dot [4]. So far, the K ondo e ect in nanostructures has been studied alm ost exclusively in relation to transport properties. In optics, K ondo e ects have only been discussed theoretically with respect to nonlinear and shake-up processes in a quantum dot [5, 6].

We present here the theory of novel e ects which arise from a combination of the K ondo e ect and the optics of nanostructures. In our model, a charged exciton in a quantum dot (QD) interacts with a Ferm i sea of free electrons. We call the resulting quasi-particles K ondo-excitons. We suggest that such novel excitons can exist in self-assem bled quantum dots where charged excitons can be prepared in voltage-tunable structures [7]. Furtherm ore, the wetting layer can be lled with electrons and used as a two-dimensional (2D) electron gas (g. 1a), o ering a simple means of generating a Ferm i sea in close proximity to a quantum dot. A signi cant point is that self-assem bled dots are very small, only a few nanom eters in diameter, allowing the K ondo tem perature T_K to be as high as 10 K.We indicate the photolum inescence (PL) from K ondo excitons is determined by the K ondo DOS at the Ferm i level such that the PL line width is equal to $k_B T_K$ (k_B is the Boltzm ann constant). Furtherm ore, the PL energy depends strongly on the Ferm i energy, and therefore also on a bias voltage. This behavior contrasts with conventional single dot PL where the lines are very sharp depending only weakly through the Stark e ect on the bias [7].

In voltage-tunable structures, self-assem bled QDs are embedded between two contacts [7, 8]. This makes it possible to control the number of electrons in a QD by application of a voltage U_g (g.1a) [8]. By generating a hole with optical excitation, it has been demonstrated that there are regions of gate voltage with constant excitonic charge, with the excitonic charge changing abruptly at particular values of U_g [7]. The charged excitons, labelled Xⁿ, contain n + 1 electrons and one hole. Excitons with n up to 3 have been observed in InA s/G aAs quantum dots [7, 9]. At higher voltages, capacitance-voltage spectroscopy shows that electrons 11 the 2D wetting layer [8]. In this case, the Ferm i energy (E_F) in the wetting layer depends linearly on U_g: we nd that $E_F = (a_o=4d) (U_g U_g^o)$, where a_o is the electrone Bohr radius, d is the distance between the back gate and wetting layer, U_g^o is the threshold gate voltage at which electrons start to 11 the wetting layer, and d a_o [8]. Existing PL results in the regime of wetting layer lling show broadenings and shifts of the PL lines [7], which we believe is some evidence of an interaction with the Ferm i sea, although this has not been analyzed in detail.

Typically, the QDX⁰ and X¹ excitons are strongly bound and exist only at gate voltages



FIG.1: (a) Schem atic of the heterostructure with a quantum dot embedded between front and back gates; d l. (b) The band diagram of a quantum dot and associated wetting layer showing also the energies typical to self-assem bled quantum dots.

where the wetting layer is empty. It is therefore unlikely that X 0 and X 1 can couple with the Ferm isea. Instead, we focus on the excitons X 2 and X 3 for which the electrons on the upper state m ay couple with extended states of the Ferm isea as we illustrate in g.lb. Since self-assem bled Q D s are usually anisotropic, we model a Q D with two bound non-degenerate orbital states, having indexes s and p. For a p state electron, the electrostatic potential consists of the Q D short-range con nem ent and the long-range C oulom b repulsion from the charges in the lower s state. This potential will therefore have a barrier at the edge of the Q D (g.1a), allowing the p electron (s) to tunnel in and out of the Q D.

To investigate the interaction between a quantum dot exciton and a Ferm isea of electrons, we employ the Anderson Ham iltonian which includes the single-particle energy \hat{H}_{sp} , the intra-dot C oulom b interaction, and a hybridization term \hat{H}_{tun} :

$$\hat{H} = \hat{H}_{sp} + \frac{1}{2} X_{1; 2; 3; 4} U_{1; 2; 3; 4}^{ee} a_{1}^{*} a_{2}^{+} a_{3}^{*} a_{4}^{*} X_{1; 2; 3; 4}^{eh} U_{1; 2; 3; 4}^{eh} a_{1}^{+} b_{2}^{+} b_{3}^{*} a_{4}^{*} + \hat{H}_{tu} A_{t}^{1}$$

where a^+ (b^+) is the intra-dot creation operator of electrons (holes); U^{ee} and U^{eh} are electronelectron and electron-hole C oulom b potential matrix elements, respectively. The index stands for (;), where is the orbital index and the spin index; can be s or p, and = $\frac{1}{2}$ for electrons and $\frac{3}{2}$ for heavy holes. \hat{H}_{tun} is given by: $\hat{H}_{tun} = {}^{P} V_k [g^+_k; a_p; + a^+_p; q_k;]$, where the operators q_k ; describe the delocalized electrons in the Ferm i sea; k and E k are the 2D m omentum and kinetic energy, respectively. For the tunnel matrix element V_k , we assume $V_k = V$ in the interval $0 < E_k < D$ and $V_k = 0$ elsewhere [10]. In the operator \hat{H}_{tun} , we include only coupling between the p state and the Ferm i sea. In our approach,



FIG. 2: (a) Calculated energy of the initial state as a function of the delocalized state energy. The energy E_F plays the role of the Ferm i level. Here, $U_{dot} = 64 \text{ m eV}$ and E_g is the band gap of the QD. (b) E lectron con gurations contributing to the initial ground state. E lectron (hole) spins are represented with solid (open) triangles.

the quantization in a QD is assumed to be strong so that the Coulomb interactions can be included with perturbation theory [11, 12]. The tunnel broadening is the sm allest energy in the problem . Our approach is to solve eq. 1 for the initial and nal states, and calculate the optical emission spectrum at zero temperature:

$$I(!) = Re_{0}^{Z_{1}} dte^{i!t} < ij\hat{V}_{0}^{+}(t)\hat{V}_{0}(0)ji > ;$$

where $ji > is the initial state and the operator <math>\hat{V_o} = V_{opt} (b_{s; \frac{3}{2}} a_{s;"} + b_{s;\frac{3}{2}} a_{s;#} + cc:)$ describes the strong transitions between the hole and electron s states.

We start with a zero bandwidth model, in which the Ferm i sea is replaced by a single \debcalized" state of energy E_F [1]. In this simplied model, E_F plays the role of the Ferm i level allowing us to predict the main features in the evolution of the PL with Ferm i energy. We describe the electron wave function with the occupations of the electron states, labelling the debcalized state e. The aim is explore the hybridization of the X² and X³ excitons, so we consider 4 electrons and one hole. We take the hole angular momentum as $+\frac{3}{2}$ (denoted $s_{+\frac{3}{2}}$); equivalent results are obtained also with $\frac{3}{2}$. The electron wave function of the hybridized initial state before photon emission will have total electron spin $S_e = 0$. We therefore express the ground state as $j_L > = A_1 j_A > +A_2 j_2 >$, where:

The states $ji_1 > and jj_2 > correspond to the excitons X² and X³, respectively (g.2), and have energies E_{i1} and E_{i2}. In the K ondo function <math>ji_1 >$, the delocalized electron \screens" the net spin in the QD. By diagonalising the H am iltonian, we not that the initial ground state has energy E_i = $\frac{1}{2}$ (E_{i1} + E_{i2} $(E_{i1} - E_{i2})^2 + 8V^2$) and that A₁ = $a = (1 + a^2)^{1=2}$, A₂ = A₁=a, where a = (E_{i2} E_i) = $\frac{1}{2}V$.

As the energy E_F increases, the ground state evolves from the X² to the X³ exciton. The transition occurs when E_{i_1} E_{i_2} where E_F $E_{1! 2} = E_2^{intra}$ E_1^{intra} where E_1^{intra} and E_2^{intra} are the intra-dot energies. The hybridization between j_4 > and j_2 > corresponds to the so-called mixed-valence regime [1]. To calculate E_i num erically, we represent a QD as an anisotropic harm onic oscillator taking the electron (hole) oscillator frequencies as 25 and 20 (12.5 and 10) m eV.Fig. 2a shows E_i as a function of E_F .

A fler photon emission from state $j_{i} >$, the nal state $j_{f} >$ has $S_{e} = \frac{1}{2}$. The intradot con guration in the X² nal state is either a singlet ($S_{dot} = 0$), with con guration $\frac{p^{1}}{2}$ ($j_{5"}; p_{\#} > j_{\#}; p_{"} >$), or a triplet ($S_{dot} = 1$), with con gurations $j_{5"}; p_{"} >$ and $\frac{p^{1}}{2}$ ($j_{5"}; p_{\#} > \frac{p_{\#}; p_{"} >}{p_{\#}; p_{"} >}$) [7] (Fig. 3a). The PL related to these con gurations are well separated, typically by 5 m eV [7, 9], due to the exchange interaction between the s and p states. Non-zero optical matrix elements exist for the three nal states:

$$jf_{1} > = \frac{1}{p_{-}} (j_{B^{n}}; p_{\#}; e_{\pi} > + j_{B^{\#}}; p_{\pi}; e_{\pi} > 2j_{B^{*}}; p_{\pi}; e_{\#} >);$$

$$jf_{2} > = \frac{1}{p_{-}} (j_{B^{n}}; p_{\#}; e_{\pi} > - j_{B^{*}}; p_{\pi}; e_{\pi} >);$$

$$jf_{3} > = -j_{B^{n}}; p_{\pi}; p_{\#} > :$$

In the state $jf_1 >$, the intra-dot triplet state with $S_{dot} = 1$ is \screened" by the delocalized electron. $jf_2 >$ has the singlet intra-dot state, and the function $jf_3 >$ plays the main role in the emission of the X³ exciton.

The calculated PL spectrum contains three lines (Fig.3), labelled as X $_{\rm t}^2$, X $_{\rm s}^2$ and X 3 , with relative intensities $\frac{3}{4}A_1^2:\frac{1}{4}A_1^2:A_2^2$. Without the tunnel interaction, there is an abrupt jump in the PL from X 2 to X 3 , but with the tunnel interaction, the PL shows very clearly hybridization e ects. In particular, in the mixed-valence regime E $_{\rm F}$ E_{1! 2}, the intensity of the X 2 lines rapidly decrease and the X 3 line appears but the energies of all three lines depend on the delocalized state energy E $_{\rm F}$. Hence, a clear prediction is that in the hybridization regime, the PL depends on the Ferm i energy and therefore also on the gate voltage.

We focus now on the PL line shapes in the K ondo regime $E_F < E_{1!2}$. While the zero bandwidth model is adequate for the general picture of the PL, we have to employ the nite bandwidth model in order to calculate the PL line shapes. The initial K ondo state is the exciton X² coupled with the Fermi sea. A trial function for the $S_e = 0$ ground state is [1, 13]:

$$j_{i} > = [A_{0}j_{0} > + X_{k} A_{k}j_{k} >] \quad j_{2} = \frac{3}{2} > ;$$
(2)



FIG.3: (a) Final intra-dot states related to the singlet and triplet states of the X² exciton, and to the X³ exciton. (b) C alculated energies of the optical transitions as a function of the delocalized state energy without (V = 0) and with (V = 0.5 m eV) the hybridization. The thickness of the line represents the intensity of the emission.

$$j_{0} > = j_{B^{n}}; s_{\#}; p_{\#}; >; j_{k} > = \frac{1}{p_{-}^{2}} c_{k;\#}^{+} j_{B^{n}}; s_{\#}; p_{\pi}; > c_{k;\pi}^{+} j_{B^{n}}; s_{\#}; p_{\#}; >;$$

as represented diagram m atically in Fig. 4a. The con gurations are described with the localized states and with the symbol which denotes all states of the Ferm i sea with $k < k_F$, where k_F is the Ferm im on entum. From the Anderson Ham iltonian, we nd that [1]:

$$A_{k} = \frac{P \overline{2} V A_{0}}{E_{1}^{intra} + E_{k} - E_{i}}; A_{0} = \frac{1}{(1 + 2 =)^{1=2}};$$

where = V^2 (is the 2D DOS). We write the ground state energy as $E_i = E_1^{intra} + E_F$ where is the lowering of energy due to the K ondo e ect. If $\langle E_{1!2} E_F$, we obtain

$$= (D \quad E_{\rm F}) \exp \left(\frac{(E_2^{\rm intra} \quad E_1^{\rm intra} \quad E_{\rm F})}{2} \right)^{\rm intra} = k_{\rm B} T_{\rm K} : \qquad (3)$$

Here, the energy plays the role of the K ondo tem perature in the initial state, T_K . The tem perature T_K can be as high as 7 14 K for realistic parameters $F_F = 2$ 3:6 m eV, = 1 m eV, and D 30 m eV.

In the regime $E_F < E_{1!2}$, the nalintra-dot con guration is either a singlet or a triplet state (g. 3a), as in the case of the zero bandwidth calculation. The triplet state couples with the Fermigas, leading to a state with total electron spin $S_e = \frac{1}{2}$. However, the Kondo



FIG.4: (a) Contributions to the initial state (2); (b) Calculated emission spectrum of the X 2 exciton with the triplet nalstate con guration; = 1 m eV. The Ferm ienergies of 2 and 3:6 m eV correspond to K T_K = 7 and 14 K, respectively.

tem perature for this nal state turns out to be much less than T_K allowing us to use the single-particle nal states to calculate the PL spectrum. The singlet nal state, and also the X³ nal state, have higher energy and are broadened by energy through tunnelling into empty delocalized states. From state ji > in eq. 2, we write the spectral function I (!) in the form :

$$I(!) = Re[i_{:\circ}^{X} A A \circ F; \circ];$$

where can be either 0 or k, $F_{\circ} = \langle \hat{y}_{\circ}^{+} \hat{R} \hat{V}_{\circ} j_{\circ} \rangle$, and $\hat{R} = 1 = (\hat{H} + h! E_{i} i0)$. We nd that the X_{t}^{2} PL line has an asymmetric shape (Fig. 4):

$$X_{t}^{2} (!) = V_{opt}^{2} \frac{3 A_{0}^{2}}{2} \int_{0}^{Z_{D}} d \frac{1}{(+k_{B} T_{K})^{2}} Re \frac{i}{h! E^{0}(X_{t}^{2}) + i}; \quad (4)$$

where $E^{0}(X_{t}^{2}) = E(X_{t}^{2})$ $k_{B}T_{K}$ is the renormalized emission energy and describes the broadening of the nal state. We can expect to be small since the relaxation of the nal state requires a spin-ip [7], and in this case, $k_{B}T_{K}$ t, PL line width is equal to K T_{K} . In other words, the PL rejects the spectral DOS near the Fermi level in the initial K ondo state.

The important result is that in the K ondo regime, both the PL peak position and the PL line shape depend on the Ferm ienergy and, hence, on the gate voltage. Furtherm ore, as the tem perature increases, the peak in the spectral DOS diminishes rapidly [1] and therefore the line width of the K ondo-exciton X_t^2 should also be strongly tem perature dependent.

In the general case of arbitrary E_F , the nite bandwidth model leads to the PL spectrum similar to that in g.3b [14]. The X $_s^2$ and X 3 PL lines are close to Lorentzians, with line widths of due to the nite lifetime of the nal states. It is important to emphasize that the X $_t^2$ nal state lies at lower energy and does not su er from tunnel broadening such that the line shape and line width are determined by many-body e ects.

In summary, we have described novel excitons which can exist in self-assembled QDs when there is an interaction between a charged exciton localized on the dot and delocalized electrons in the wetting layer. The charged exciton with nonzero spin is surrounded by a \cloud" (of radius / $(k_B T_K)^{-1}$) of Ferm i electrons. We predict several striking manifestations of these novel states in the emission spectra: at low temperature, the optical lines are strongly dependent on vertical bias and their widths are determined by the K ondo temperature.

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- A.C.Hewson, The Kondo Problem to Heavy Fermions (Cambridge University Press, Cambridge, 1993).
- [2] V. Madhavan, W. Chen, T. Jam neala, M. F. Crommie, and N. S. Wingreen, Science 280, 567 (1998); J. Park, A. N. Pasupathy, J. I. Goldsmith, C. Chang, Y. Yaish, J. R. Petta, M. Rinkoski, J. P. Sethna, H. D. Abruma, P. L. McEuen, and D. C. Ralph, Nature 417, 722 (2002); W. Liang, M. P. Shores, M. Bockrath, J. R. Long, and H. Park, Nature 417, 725 (2002).
- [3] D.Goldhaber-Gordon, H.Shtrikm an, D.Mahalu, D.Abusch-Magder, U.Meirav, and M.A. Kastner, Nature (London) 391, 156 (1998); S.M.Cronenwett, T.H.Oosterkamp, and L. P.Kouwenhoven, Science 281, 540 (1998); J.Schmid, J.Weis, K.Eberl, and K.v.Klitzing, Phys.Rev.Lett. 84, 5824 (2000); F.Simmel, R.H.Blick, J.P.Kotthaus, W.Wegscheider, and M.Bichler, Phys.Rev.Lett. 83, 804 (1999).
- [4] W.G.van der Wiel, S.De Franceschi, T.Fujisawa, J.M.Elzerman, S.Tarucha, and L.P. Kouwenhoven, Science 289, 2105 (2000).
- [5] T.V.Shahbazyan, I.E.Perakis, and M.E.Raikh, Phys. Rev. Lett. 84, 5896 (2000).
- [6] K.Kikoin and Y.Avishai, Phys. Rev. B 62, 4647 (2000).
- [7] R.J.W arburton, C.Scha ein, D.Haft, F.Bickel, A.Lorke, K.Karral, J.M.Garcia, W. Schoenfeld, P.M. Petro, Nature (London) 405, 926 (2000).
- [8] R. J. Luyken, A. Lorke, A. O. Govorov, J. P. Kotthaus, G. Medeiros-Ribeiro, and P. M. Petro, Appl. Phys. Lett. 74, 2486 (1999).
- [9] F.Findeis, M.Baier, A.Zrenner, M.Bichler, G.Abstreiter, U.Hohenester, and E.Molinari,

Phys.Rev.B 63, 121309 (2001); J.J.Finley, A.D.Ashmore, A.Lemaître, D.J.Mowbray, M.S.Skolnick, I.E.Itskevich, P.A.Maksym, M.Hopkinson, and T.F.K rauss, Phys.Rev. B 63, 073307 (2001).

- [10] The matrix element V_k decreases with kinetic energy E_k since the wave functions of delocalized electrons oscillate. The cut-o parameter D can be estimated as $h^2 = m L^2$, where L and m are the QD lateral size and electron mass, respectively.
- [11] A.O.G ovorov and A.V.Chaplik, Sov.Phys.JETP, 72, 1037 (1991).
- [12] R.J.W arburton, B.T.M iller, C.S.Duerr, C.Boedefeld, K.Karrai, J.P.K otthaus, G.M edeiros-Ribeiro, P.M. Petro, and S.Huant, Phys. Rev. B 58, 16221 (1998).
- [13] O.Gunnarsson and K.Schonhammer, Phys. Rev. B 28, 4315 (1983).
- [14] M ore details related to the nite bandwidth m odel will be published elsewhere.